

NPN RF POWER TRANSISTOR

DESCRIPTION:

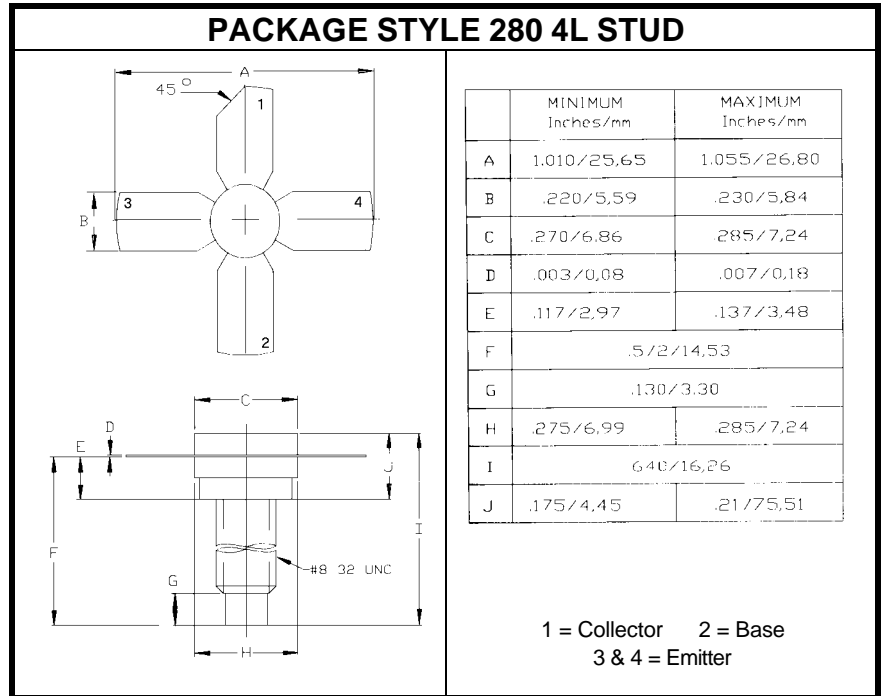
The **TPM401** is a Common Emitter Device Designed for Class A and AB Amplifier Applications up to 1.0 GHz.

FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	400 mA
V_{CB0}	40 V
P_{DISS}	8.75 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	20 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 1.0 mA	40			V
BV_{CEO}	I _C = 1.0 mA	28			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	20		120	---
C_{OB}	V _{CB} = 28 f = 1.0 MHz			5.0	pF
P_G	V _{CE} = 24 V I _C = 200 mA f = 400 MHz P _{OUT} = 1.0 W	13	15		dB
P_{1dB}	V _{CE} = 24 V I _C = 200 mA f = 400 MHz		2.0		W